Tadatomo T Suga

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

415	5,868	41	62
papers	citations	h-index	g-index

551	7,037	2.2	5.79
ext. papers	ext. citations	avg, IF	L-index

#	Paper	IF	Citations
415	A novel strategy for GaN-on-diamond device with a high thermal boundary conductance. *Journal of Alloys and Compounds*, **2022**, 905, 164076	5.7	4
414	Hydrophilic nanoporous copper surface prepared by modified formic acid vapor treatment. *Surfaces and Interfaces*, **2022**, 28, 101620	4.1	0
413	Thermodynamics of Ion-Cutting of �Ga2O3 and Wafer-Scale Heterogeneous Integration of a �Ga2O3 Thin Film onto a Highly Thermal Conductive SiC Substrate. *ACS Applied Electronic Materials* , **2022**, 4, 494-502	4	4
412	Direct Cu to Cu Bonding and Alternative Bonding Techniques in 3D Packaging. *Springer Series in Advanced Microelectronics*, **2021**, 201-231	1	0
411	Efficient thermal dissipation in wafer-scale heterogeneous integration of single-crystalline �Ga2O3 thin film on SiC. *Fundamental Research*, **2021**, 1, 691-691		4
410	Channel Properties of Ga��on-SiC MOSFETs. *IEEE Transactions on Electron Devices*, **2021**, 68, 1185-1189	2.9	6
409	Evidence for intermolecular forces involved in ladybird beetle tarsal setae adhesion. *Scientific Reports*, **2021**, 11, 7729	4.9	4
408	A Novel Preparation of Ag Agglomerates Paste with Unique Sintering Behavior at Low Temperature. *Micromachines*, **2021**, 12,	3.3	1
407	Sequential Plasma Activation for Low Temperature Bonding of Aluminosilicate Glass. *ECS Journal of Solid State Science and Technology*, **2021**, 10, 054007	2	0
406	Enhancement and Mechanism of Copper Nanoparticle Sintering in Activated Formic Acid Atmosphere at Low Temperature. *ECS Journal of Solid State Science and Technology*, **2021**, 10, 054004	2	2
405	Thermal Visualization of Buried Interfaces Enabled by Ratio Signal and Steady-State Heating of Time-Domain Thermoreflectance. *ACS Applied Materials & Interfaces*, **2021**, 13, 31843-31851	9.5	9
404	Heterogeneous GaN-Si integration via plasma activation direct bonding. *Journal of Alloys and Compounds*, **2021**, 852, 156933	5.7	5
403	Room Temperature Wafer Bonding of Glass Using Aluminum Oxide Intermediate Layer. *Advanced Materials Interfaces*, **2021**, 8, 2001741	4.6	3
402	Transfer of Ferroelectric Thin Film Capacitor Using Internal Stress of Plated Film. *IEEJ Transactions on Sensors and Micromachines*, **2021**, 141, 39-43	0.2	
401	Silicate glass-to-glass hermetic bonding for encapsulation of next-generation optoelectronics: A review. *Materials Today*, **2021**, 47, 131-155	21.8	2
400	Demonstration of high thermal performance GaN-on-graphite composite bonded substrate for application in III-V nitride electronics. *Applied Physics Express*, **2021**, 14, 091002	2.4	1
399	Fabrication of Ag@Ag2O-MnOx composite nanowires for high-efficient room-temperature removal of formaldehyde. *Journal of Materials Science and Technology*, **2021**, 91, 5-16	9.1	4

398	Effect of Au Film Thickness and Surface Roughness on Room-Temperature Wafer Bonding and Wafer-Scale Vacuum Sealing by Au-Au Surface Activated Bonding. *Micromachines*, **2020**, 11,	3.3	9
397	Rapid pressureless and low-temperature bonding of large-area power chips by sintering two-step activated Ag paste. *Journal of Materials Science: Materials in Electronics*, **2020**, 31, 6497-6505	2.1	5
396	Room-temperature pressureless wafer-scale hermetic sealing in air and vacuum using surface activated bonding with ultrathin Au films. *Japanese Journal of Applied Physics*, **2020**, 59, SBBB01	1.4	2
395	Robust Ag-Cu Sintering Bonding at 160 °C via Combining Ag2O Microparticle Paste and Pt-Catalyzed Formic Acid Vapor. *Metals*, **2020**, 10, 315	2.3	6
394	Recycled low-temperature direct bonding of Si/glass and glass/glass chips for detachable micro/nanofluidic devices. *Journal of Materials Science and Technology*, **2020**, 46, 156-167	9.1	10
393	Enhanced adhesion and anticorrosion of silk fibroin coated biodegradable Mg-Zn-Ca alloy via a two-step plasma activation. *Corrosion Science*, **2020**, 168, 108466	6.8	16
392	Interfacial Thermal Conductance across Room-Temperature-Bonded GaN/Diamond Interfaces for GaN-on-Diamond Devices. *ACS Applied Materials & Interfaces*, **2020**, 12, 8376-8384	9.5	51
391	�Ga2O3 MOSFETs on the Si substrate fabricated by the ion-cutting process. *Science China: Physics, Mechanics and Astronomy*, **2020**, 63, 1	3.6	15
390	Emerging wafer bonding technologies **2020**, 627-639		
389	Direct bonding of high dielectric oxides for high-performance transistor applications. *Scripta Materialia*, **2020**, 178, 307-312	5.6	13
388	Exploration of the enhanced performances for silk fibroin/sodium alginate composite coatings on biodegradable Mg�Zn�Ca alloy. *Journal of Magnesium and Alloys*, **2020**, 9, 1578-1578	8.8	8
387	Direct Bonding of GaN to Diamond Substrate at Room Temperature **2020**,		1
386	Thermal Transport across Ion-Cut Monocrystalline �GaO Thin Films and Bonded �GaO-SiC Interfaces. *ACS Applied Materials & Interfaces*, **2020**, 12, 44943-44951	9.5	36
385	Wafer-scale Au-Au surface activated bonding using atmospheric-pressure plasma **2019**,		0
384	**2019**,		0
383	Wafer Bonding of SiC-AlN at Room Temperature for All-SiC Capacitive Pressure Sensor. *Micromachines*, **2019**, 10,	3.3	2
382	Moir�Based Alignment Using Centrosymmetric Grating Marks for High-Precision Wafer Bonding. *Micromachines*, **2019**, 10,	3.3	2
381	High Thermal Boundary Conductance across Bonded Heterogeneous GaN-SiC Interfaces. *ACS Applied Materials & Interfaces*, **2019**, 11, 33428-33434	9.5	41

380	Low temperature Cu bonding with large tolerance of surface oxidation. *AIP Advances*, **2019**, 9, 055127	1.5	5
379	Growth Behavior of Au Films on SiO2Film and Direct Transfer for Smoothing Au Surfaces. *International Journal of Automation Technology*, **2019**, 13, 254-260	0.8	2
378	X-ray Photoelectron Spectroscopy (XPS) Analysis of Oxidation Behavior of Hydrogen-radical-treated Cu Surfaces. *IEEJ Transactions on Sensors and Micromachines*, **2019**, 139, 38-39	0.2	
377	Investigation of Plasma Treatment Conditions for Wafer-Scale Room-Temperature Bonding Using Ultrathin Au Films in Ambient Air. *IEEJ Transactions on Sensors and Micromachines*, **2019**, 139, 217-218	0.2	
376	Comparison of Argon and Oxygen Plasma Treatments for Ambient Room-Temperature Wafer-Scale Au?Au Bonding Using Ultrathin Au Films. *Micromachines*, **2019**, 10,	3.3	25
375	First Demonstration of Waferscale Heterogeneous Integration of Ga2O3 MOSFETs on SiC and Si Substrates by Ion-Cutting Process **2019**,		22
374	De-bondable SiC SiC wafer bonding via an intermediate Ni nano-film. *Applied Surface Science*, **2019**, 465, 591-595	6.7	8
373	Direct wafer bonding of Ga2O3SiC at room temperature. *Ceramics International*, **2019**, 45, 6552-6555	5.1	25
372	Room temperature bonding and debonding of polyimide film and glass substrate based on surface activate bonding method. *Japanese Journal of Applied Physics*, **2018**, 57, 02BB05	1.4	2
371	Graphene transfer by surface activated bonding with poly(methyl glutarimide). *Japanese Journal of Applied Physics*, **2018**, 57, 02BB02	1.4	1
370	Evaluation of hydrogen radical treatment for indium surface oxide removal and analysis of re-oxidation behavior. *Japanese Journal of Applied Physics*, **2018**, 57, 02BC01	1.4	2
369	Bonding and transferring of carbon nanotube bumps using magnetron sputtering. *Japanese Journal of Applied Physics*, **2018**, 57, 02BC02	1.4	
368	Study of Cu Film Surface Treatment Using Formic Acid Vapor/Solution for Low Temperature Bonding. *Journal of the Electrochemical Society*, **2018**, 165, H3080-H3084	3.9	7
367	Direct Homo/Heterogeneous Bonding of Silicon and Glass Using Vacuum Ultraviolet Irradiation in Air. *Journal of the Electrochemical Society*, **2018**, 165, H3093-H3098	3.9	18
366	Sequential plasma activation methods for hydrophilic direct bonding at sub-200 °C. *Japanese Journal of Applied Physics*, **2018**, 57, 02BD03	1.4	16
365	Mechanism of bonding and debonding using surface activated bonding method with Si intermediate layer. *Japanese Journal of Applied Physics*, **2018**, 57, 04FC11	1.4	4
364	Properties of various plasma surface treatments for low-temperature AuAu bonding. *Japanese Journal of Applied Physics*, **2018**, 57, 04FC12	1.4	8
363	Room temperature GaN-diamond bonding for high-power GaN-on-diamond devices. *Scripta Materialia*, **2018**, 150, 148-151	5.6	48

362	Low-temperature wafer direct bonding of silicon and quartz glass by a two-step wet chemical surface cleaning. *Japanese Journal of Applied Physics*, **2018**, 57, 02BD02	1.4	8
361	Surface Activated Bonding Method for Low Temperature Bonding **2018**,		2
360	Strain Effect in Highly-Doped n-Type 3C-SiC-on-Glass Substrate for Mechanical Sensors and Mobility Enhancement. *Physica Status Solidi (A) Applications and Materials Science*, **2018**, 215, 1800288	1.6	4
359	Direct wafer bonding of GaN-SiC for high power GaN-on-SiC devices. *Materialia*, **2018**, 3, 12-14	3.2	14
358	(Invited) Room Temperature Wafer Bonding of Wide Bandgap Semiconductors. *ECS Transactions*, **2018**, 86, 3-21	1	1
357	Room temperature GaN bonding by surface activated bonding methods **2018**,		1
356	Low temperature de-oxidation for copper surface by catalyzed formic acid vapor. *Applied Surface Science*, **2018**, 456, 890-898	6.7	6
355	Reduction reaction analysis of nanoparticle copper oxide for copper direct bonding using formic acid. *Japanese Journal of Applied Physics*, **2017**, 56, 04CC01	1.4	11
354	Room Temperature SiC-SiO_2Wafer Bonding Enhanced by Using an Intermediate Si Nano Layer. *ECS Journal of Solid State Science and Technology*, **2017**, 6, P227-P230	2	7
353	GaN-Si direct wafer bonding at room temperature for thin GaN device transfer after epitaxial lift off. *Applied Surface Science*, **2017**, 416, 1007-1012	6.7	23
352	A Comparative Study: Void Formation in Silicon Wafer Direct Bonding by Oxygen Plasma Activation with and without Fluorine. *ECS Journal of Solid State Science and Technology*, **2017**, 6, P7-P13	2	18
351	Room temperature bonding and debonding of PI film and glass substrate based on SAB method **2017**,		1
350	Room-temperature direct bonding of silicon and quartz glass wafers. *Applied Physics Letters*, **2017**, 110, 221602	3.4	22
349	Combined surface activated bonding using H-containing HCOOH vapor treatment for Cu/Adhesive hybrid bonding at below 200 °C. *Applied Surface Science*, **2017**, 414, 163-170	6.7	9
348	Room-Temperature Bonding of Wafers with Smooth Au Thin Films in Ambient Air Using a Surface-Activated Bonding Method. *IEICE Transactions on Electronics*, **2017**, E100.C, 156-160	0.4	21
347	Ar+H_2 atmospheric-pressure plasma treatment for Au-Au bonding and influence of air exposure on surface contamination **2017**,		1
346	Low temperature Cu-Cu bonding by transient liquid phase sintering of mixed Cu nanoparticles and Sn-Bi eutectic powders. *Journal of Materials Science: Materials in Electronics*, **2017**, 28, 16433-16443	2.1	9
345	Hydrogen radical treatment for indium surface oxide removal and re-oxidation behaviour **2017**,		3

344	Single-Crystalline 3C-SiC anodically Bonded onto Glass: An Excellent Platform for High-Temperature Electronics and Bioapplications. *ACS Applied Materials & Interfaces*, **2017**, 9, 27365-27371	9.5	41
343	Room-temperature transfer bonding of lithium niobate thin film on micromachined silicon substrate with Au microbumps. *Sensors and Actuators A: Physical*, **2017**, 264, 274-281	3.9	14
342	2D material transfer using room temperature bonding **2017**,		1
341	Room Temperature Bonding with Polymethylglutarimide Using the Surface Activated Bonding Method for a Layer Transfer Platform. *ECS Journal of Solid State Science and Technology*, **2017**, 6, P512-P516	2	7
340	Introduction to the innovative interface bonding technology **2017**,		1
339	Novel sequential plasma activation method for direct glass bonding **2017**,		2
338	Mechanisms for Room-Temperature Fluorine Containing Plasma Activated Bonding. *ECS Journal of Solid State Science and Technology*, **2017**, 6, P373-P378	2	15
337	Hydrogen radical treatment of printed indium solder paste for bump formation **2017**,		1
336	Cu/Adhesive Hybrid Bonding at 180 °C in H-Containing HCOOH Vapor Ambient for 2.5D/3D Integration **2017**,		2
335	Room Temperature Temporary Bonding of Glass Substrates Based on SAB Method Using Si Intermediate Layer. *IEEE Transactions on Components, Packaging and Manufacturing Technology*, **2017**, 7, 1713-1720	1.7	8
334	Direct Cu to Cu Bonding and Other Alternative Bonding Techniques in 3D Packaging. *Springer Series in Advanced Microelectronics*, **2017**, 129-155	1	10
333	Surface Activated Bonding and Debonding of Polymer Films and Glasses Using Si Nano-Adhesion Layer. *Hyomen Kagaku*, **2017**, 38, 67-71		
332	Room-Temperature Gold-Gold Bonding Method Based on Argon and Hydrogen Gas Mixture Atmospheric-Pressure Plasma Treatment for Optoelectronic Device Integration. *IEICE Transactions on Electronics*, **2016**, E99.C, 339-345	0.4	11
331	Direct Wafer Bonding of SiC-SiC by SAB for Monolithic Integration of SiC MEMS and Electronics. *ECS Journal of Solid State Science and Technology*, **2016**, 5, P451-P456	2	12
330	Combined Surface Activated Bonding Technique for Hydrophilic SiO2-SiO2 and Cu-Cu Bonding. *ECS Transactions*, **2016**, 75, 117-128	1	4
329	Combined Surface Activated Bonding Technique for Low-Temperature Cu/Dielectric Hybrid Bonding. *ECS Journal of Solid State Science and Technology*, **2016**, 5, P419-P424	2	20
328	The study of Cu-Cu low temperature bonding using formic acid treatment with/without Pt catalyst **2016**,		2
327	Room-temperature wafer bonding of SiC□Si by modified surface activated bonding with sputtered Si nanolayer. *Japanese Journal of Applied Physics*, **2016**, 55, 04EC09	1.4	13

326	Surface Activation and Planarization with Gas Cluster Ion Beam for Wafer Bonding. *ECS Transactions*, **2016**, 75, 9-13	1	3
325	Modified Surface Activated Bonding Using Si Intermediate Layer for Bonding and Debonding of Glass Substrates. *ECS Transactions*, **2016**, 75, 185-189	1	4
324	Nanomechanical Analysis of Polydimethylglutarimide Based Lift Off Resist Used for Temporary Bonding and Film Transfers. *ECS Transactions*, **2016**, 75, 191-196	1	
323	Communication Fluorinated Plasma Treatments Using PTFE Substrates for Room-Temperature Silicon Wafer Direct Bonding. *ECS Journal of Solid State Science and Technology*, **2016**, 5, P393-P395	2	4
322	Room-temperature wafer bonding using smooth gold thin films for wafer-level MEMS packaging **2016**,		1
321	Review of Low-Temperature Bonding Technologies and Their Application in Optoelectronic Devices. *Electronics and Communications in Japan*, **2016**, 99, 63-71	0.4	14
320	A Review of Low-temperature Sealing Technologies using Metal Thin Films and Solders for Sensors and MEMS. *IEEJ Transactions on Sensors and Micromachines*, **2016**, 136, 266-273	0.2	3
319	Contact Behavior among Vertically Aligned Carbon Nanotube Bumps under Compression for Flexible Multilayer Substrates. *ECS Journal of Solid State Science and Technology*, **2016**, 5, M83-M87	2	1
318	Combined surface-activated bonding technique for low-temperature hydrophilic direct wafer bonding. *Japanese Journal of Applied Physics*, **2016**, 55, 04EC02	1.4	7
317	Direct Wafer Bonding of SiC-SiC at Room Temperature by SAB Method. *ECS Transactions*, **2016**, 75, 77-83	1	3
316	A Scalable Clean Graphene Transfer Process Using Polymethylglutarimide as a Support Scaffold. *Journal of the Electrochemical Society*, **2016**, 163, E159-E161	3.9	13
315	Transient liquid-phase sintering using silver and tin powder mixture for die bonding. *Japanese Journal of Applied Physics*, **2016**, 55, 04EC14	1.4	23
314	Room Temperature Bonding and Debonding of Ultra-Thin Glass Substrates for Fabrication of LCD **2016**,		2
313	A comparison study: Direct wafer bonding of SiC SiC by standard surface-activated bonding and modified surface-activated bonding with Si-containing Ar ion beam. *Applied Physics Express*, **2016**, 9, 081302	3.4	22
312	Direct bonding for dissimilar metals assisted by carboxylic acid vapor. *Japanese Journal of Applied Physics*, **2015**, 54, 030217	1.4	3
311	Silicon carbide wafer bonding by modified surface activated bonding method. *Japanese Journal of Applied Physics*, **2015**, 54, 030214	1.4	21
310	Novel hydrophilic SiO2wafer bonding using combined surface-activated bonding technique. *Japanese Journal of Applied Physics*, **2015**, 54, 030218	1.4	5
309	Surface activated bonding of GaAs and SiC wafers at room temperature for improved heat dissipation in high-power semiconductor lasers. *Japanese Journal of Applied Physics*, **2015**, 54, 030207	1.4	26

308	Fabrication of carbon nanotube bump interconnects for flexible multilayer substrates. *Japanese Journal of Applied Physics*, **2015**, 54, 030205	1.4	1
307	Fast atom bombardment onto vertically aligned multi-walled carbon nanotube bumps to achieve low interconnect resistance with Au layer. *Microelectronics Reliability*, **2015**, 55, 2560-2564	1.2	4
306	Effect of ion species for the surface activated bonding of GaAs wafers on the characteristics of the bonded interfaces **2015**,		1
305	Surface activated bonding between bulk single crystal diamond and bulk aluminum. *Japanese Journal of Applied Physics*, **2015**, 54, 081301	1.4	4
304	Room temperature direct bonding and debonding of polymer film on glass wafer for fabrication of flexible electronic devices **2015**,		2
303	Room-temperature bonding method for polymer substrate of flexible electronics by surface activation using nano-adhesion layers. *Japanese Journal of Applied Physics*, **2015**, 54, 101602	1.4	14
302	Dielectric Spectroscopic Detection of Early Failures in 3-D Integrated Circuits. *ECS Transactions*, **2015**, 69, 79-88	1	1
301	Room Temperate Bonding of Al2O3 Layers by Atomic Layer Deposition on Polyimide Substrates. *ECS Transactions*, **2015**, 69, 99-105	1	2
300	Process parameters for formic acid treatment with Pt catalyst for Cu direct bonding **2015**,		3
299	Nanobonding: A key technology for emerging applications in health and environmental sciences. *Japanese Journal of Applied Physics*, **2015**, 54, 030201	1.4	6
298	Room-temperature direct bonding of germanium wafers by surface-activated bonding method. *Japanese Journal of Applied Physics*, **2015**, 54, 030213	1.4	8
297	Low temperature Au-Au surface-activated bonding using nitrogen atmospheric-pressure plasma treatment for optical microsystems **2015**,		3
296	Influence of air exposure time on bonding strength in Au-Au surface activated wafer bonding **2015**,		2
295	Room-Temperature Wafer Bonding for High-Heat Dissipation Structure in High-Power Semiconductor Devices. *Journal of Japan Institute of Electronics Packaging*, **2015**, 18, 463-468	0.1	
294	Low temperature bonding for 3D **2014**,		1
293	SiC wafer bonding by modified suface activated bonding method **2014**,		1
292	Formic acid treatment with Pt catalyst for Cu direct and hybrid bonding at low temperature **2014**,		2
291	Room-temperature wafer bonding with smooth Au thin film in ambient air using Ar RF plasma activation **2014**,		3

290	Effect of Formic Acid Vapor In Situ Treatment Process on Cu Low-Temperature Bonding. *IEEE Transactions on Components, Packaging and Manufacturing Technology*, **2014**, 4, 951-956	1.7	16
289	Low Temperature Bonding for 3D Integration-Surface Activated Bonding (SAB). *Hyomen Kagaku*, **2014**, 35, 262-266		
288	Miniaturized polarization sensors integrated with wire-grid polarizers **2014**,		2
287	Room temperature bonding method for polymer films by surface activated bonding method using Al intermediate layer **2014**,		3
286	Surface activated Ge/GaAs wafer bonding for multi-junction solar cells **2014**,		2
285	Formic acid treatment with Pt catalyst for Cu direct bonding at low temperature **2014**,		2
284	Combined Surface-Activated Bonding (SAB) Technologies for New Approach to Low Temperature Wafer Bonding. *ECS Transactions*, **2014**, 64, 83-93	1	
283	Plasma assisted bonding of copper and silver substrates **2014**,		1
282	Low-Temperature Solid-State Bonding Using Hydrogen Radical Treated Solder for Optoelectronic and MEMS Packaging. *ECS Transactions*, **2014**, 64, 267-274	1	7
281	Contact Behavior among Vertical Aligned Carbon Nanotube Bumps under Compression for Flexible Multilayer Substrates. *ECS Transactions*, **2014**, 64, 21-26	1	1
280	Novel sealing technology for organic EL display and lighting by means of modified surface activated bonding method **2014**,		1
279	Low-temperature GaAs/SiC wafer bonding with Au thin film for high-power semiconductor lasers **2014**,		4
278	Review of Low-temperature Bonding Technologies and Their Application in Optoelectronic Devices. *IEEJ Transactions on Sensors and Micromachines*, **2014**, 134, 159-165	0.2	4
277	Spalling Technology of PZT Thin Film Capacitor using Internal Stress. *IEEJ Transactions on Sensors and Micromachines*, **2014**, 134, 85-89	0.2	
276	Direct bonding of PEN at room temperature by means of surface activated bonding method using nano-adhesion layer **2013**,		7
275	Bonding of glass nanofluidic chips at room temperature by a one-step surface activation using an O2/CF4 plasma treatment. *Lab on A Chip*, **2013**, 13, 1048-52	7.2	68
274	A New Combined Process of Formic Acid Pretreatment for Low-temperature Bonding of Copper Electrodes. *ECS Transactions*, **2013**, 50, 133-138	1	2
273	A Combined Process of Formic Acid Pretreatment for Low-Temperature Bonding of Copper Electrodes. *ECS Journal of Solid State Science and Technology*, **2013**, 2, P271-P274	2	28

272	Room Temperature Bonding of Polymer to Glass Wafers Using Surface Activated Bonding (SAB) Method. *ECS Transactions*, **2013**, 50, 297-302	1	6
271	Relationship between Diffusion and Adhesion Properties of Ferroelectric Thin-Film Structure on Releasable Substrate. *Japanese Journal of Applied Physics*, **2013**, 52, 06GL16	1.4	5
270	Study on Homogeneous Wafer Level Dielectric Film Preparation Using Chemical Solution Deposition Method. *Japanese Journal of Applied Physics*, **2013**, 52, 06GL09	1.4	3
269	The Third Generation on Bonding Technologies for Design and Manufacturing. *Journal of the Japan Society for Precision Engineering*, **2013**, 79, 705-709	0.1	3
268	Fabrication of PZT Thin Film on a Detachable Board and Its Adhesion Property. *IEEJ Transactions on Sensors and Micromachines*, **2013**, 133, B320-B325	0.2	
267	Homogenizing Dielectric Film using Chemical Solution Deposition Method and Application to Wafer Level Film Preparation. *IEEJ Transactions on Sensors and Micromachines*, **2013**, 133, 303-308	0.2	
266	Low-Temperature Bonding Technologies Realizing High-Functional Optical Microsystems and Sensors. *Journal of the Japan Society for Precision Engineering*, **2013**, 79, 719-724	0.1	
265	Molecular Level Study of Negative Thick-Film Resist in MEMS by Employing a Coarse-Grained Molecular Dynamics Simulation. *IEEJ Transactions on Sensors and Micromachines*, **2013**, 133, 320-329	0.2	
264	Nanoadhesion layer for enhanced Si–Si and Si–SiN wafer bonding. *Microelectronics Reliability*, **2012**, 52, 342-346	1.2	21
263	Investigation of fluorine containing plasma activation for room-temperature bonding of Si-based materials. *Microelectronics Reliability*, **2012**, 52, 347-351	1.2	20
262	Low-Temperature Bonding of GaN on Si Using a Nonalloyed Metal Ohmic Contact Layer for GaN-Based Heterogeneous Devices. *IEEE Journal of Quantum Electronics*, **2012**, 48, 182-186	2	7
261	Low-temperature direct bonding of glass nanofluidic chips using a two-step plasma surface activation process. *Analytical and Bioanalytical Chemistry*, **2012**, 402, 1011-8	4.4	65
260	Behaviors of flexible vertically aligned carbon nanotube bumps under compression **2012**,		2
259	Low-temperature hermetic packaging for microsystems using Au–Au surface-activated bonding at atmospheric pressure. *Journal of Micromechanics and Microengineering*, **2012**, 22, 055026	2	31
258	Formic acid with Pt catalyst combined treatment process for Cu low temperature bonding **2012**,		1
257	Surface activated bonding and transfer of Carbon Nanotube bumps to Au substrates **2012**,		2
256	Low temperature bonding for 3D integration —A review of the surface activated bonding (SAB) **2012**,		2
255	Vapor-Assisted Surface Activation Method for Homo- and Heterogeneous Bonding of Cu, SiO2, and Polyimide at 150°C and Atmospheric Pressure. *Journal of Electronic Materials*, **2012**, 41, 2274-2280	1.9	17

254	Low-temperature bonding of laser diode chips using atmospheric-pressure plasma activation of flat topped Au stud bumps with smooth surfaces **2012**,		2
253	**2012**,		1
252	Status of bonding technology for hybrid integration - A review of the surface activated bonding (SAB) **2012**,		1
251	Direct bonding of polymer to glass wafers using surface activated bonding (SAB) method at room temperature **2012**,		5
250	Low temperature bonding for 3D interconnects **2012**,		2
249	Recent Developments in Bonding Technology for Inorganic and Organic Materials. *Journal of the Vacuum Society of Japan*, **2012**, 55, 487-492		2
248	Theory and Experiment for Capillary Condensation of Water on Metal Oxide Films in a Humid Environment Studied by Atomic Force Microscope. *IEEJ Transactions on Sensors and Micromachines*, **2012**, 132, 397-406	0.2	
247	Homogenizing and Applying Dielectric Film to Wafer-Level Film Preparation. *Transactions of the Japan Institute of Electronics Packaging*, **2012**, 5, 92-98	0.3	2
246	Anti-Stiction Coatings for MEMS Switches Based on Quantitative Evaluation of Adhesion Forces. *Journal of Japan Institute of Electronics Packaging*, **2012**, 15, 49-58	0.1	
245	Low-temperature Bonding Technologies and Their Application to Highly Functional Sensors. *Journal of Smart Processing*, **2012**, 1, 106-113	0.2	
244	Long Life and Low Consumption System for Sustainable Development **2012**, 1040-1043		
243	Fabrication and Characterization of Ferroelectric PZT and BaTiO3 Thin Films on Releasable Electrode Structures. *Transactions of the Japan Institute of Electronics Packaging*, **2012**, 5, 34-40	0.3	1
242	Air-gap structure between integrated LiNbO3 optical modulators and micromachined Si substrates. *Optics Express*, **2011**, 19, 15739-49	3.3	24
241	Si nanoadhesion layer for enhanced SiO2□SiN wafer bonding. *Scripta Materialia*, **2011**, 65, 320-322	5.6	36
240	Investigation of anti-stiction coating for ohmic contact MEMS switches with thiophenol and 2-naphthalenethiol self-assembled monolayer. *Sensors and Actuators A: Physical*, **2011**, 172, 455-461	3.9	10
239	. *IEEE Journal of Selected Topics in Quantum Electronics*, **2011**, 17, 689-703	3.8	33
238	Passive Alignment and Mounting of LiNbO$_3$ Waveguide Chips on Si Substrates by Low-Temperature Solid-State Bonding of Au. *IEEE Journal of Selected Topics in Quantum Electronics*, **2011**, 17, 652-658	3.8	30
237	**2011**,		4

236	Surface activated bonding of copper through silicon vias and gold stud bumps at room temperature. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **2011**, 29, 021007	2.9	8
235	Formic acid vapor treated Cu-Cu direct bonding at low temperature **2011**,		3
234	Low temperature Cu-Cu direct bonding using formic acid vapor pretreatment **2011**,		11
233	Room-Temperature Direct Bonding Using Fluorine Containing Plasma Activation. *Journal of the Electrochemical Society*, **2011**, 158, H525	3.9	14
232	Surface activation-based nanobonding and interconnection at room temperature. *Journal of Micromechanics and Microengineering*, **2011**, 21, 025009	2	10
231	Room temperature SiO2 wafer bonding by adhesion layer method **2011**,		11
230	An Electrode Structure for Ferroelectric Thin Films and Its Application to the Nanotransfer Method. *Transactions of the Japan Institute of Electronics Packaging*, **2011**, 4, 40-43	0.3	3
229	Comparative annealing effect on bonded wafers in air and ultrahigh vacuum for microelectromechanical systems/microfluidics packaging. *Journal of Micro/ Nanolithography, MEMS, and MOEMS*, **2010**, 9, 041107	0.7	4
228	Interfacial Behavior of Surface Activated p-GaP/n-GaAs Bonded Wafers at Room Temperature. *Electrochemical and Solid-State Letters*, **2010**, 13, H61		24
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15	Behavior of surface oxide and intermetallic compounds in interconnections of micro Sn-Ag solder bumps		1
14	Design and fabrication of an electrostatically actuated MEMS probe card		5
13	Room temperature vacuum sealing using surface activated bonding method		12
12	Surface Activated Bonding --- High Density Packaging Solution for Advanced Microelectronic System		1
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10	A lamination technique of LCP/Cu for electronic packaging		5
9	Panel-size component integration (PCI) with molded liquid crystal polymer (LCP) substrates		5
8	Reliability and microstructure of Au-Al and Au-Cu direct bonding fabricated by the Surface Activated Bonding		4
7	Surface activated bonding for new flip chip and bumpless interconnect systems		12
6	Room-temperature interconnection of electroplated Au microbump by means of surface activated bonding method		4
5	Bump-less interconnect for next generation system packaging		11
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3	Bonding of p-Si/n-InP wafers through surface activated bonding method at room temperature		2

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